

ZDT1048 SM-8 Dual NPN medium power high gain transistors

Summary

BV_{CEO} > 17.5V I_{C(cont)} = 5A V_{CE(sat)} < 75mV @ 1A P_D = 2.75W

Description

Advanced process capability has been used to achieve this high performance device. Combining two NPN transistors in the SM-8 package provides a compact solution for the intended applications.

Features

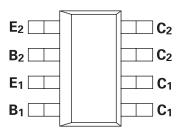
- Dual NPN device
- Very low saturation voltage
- High gain
- SM 8 package

Applications

- CCFL invertors
- Royer circuits

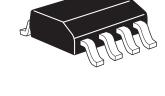
Ordering information

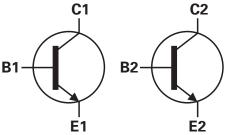
DEVICE	Reel size	Tape width	Quantity
	(inches)	(mm)	per reel
ZDT1048TA	7	12	1000



Device marking

T1048





Absolute maximum ratings

Parameter	Symbol	Value	Unit
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CEO}	17.5	V
Emitter-base voltage	V _{EBO}	5	V
Peak pulse current	I _{CM}	20	А
Continuous collector current	۱ _C	5	А
Base current	Ι _Β	500	mA
Operating and storage temperature range	T _j :T _{stg}	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Total power dissipation at T _{amb} = 25°C*	P _{tot}		
Any single die "on"		2.25	W
Both die "on" equally		2.75	W
Derate above 25°C*			V
Any single die "on"		18	mW/°C
Both die "on" equally		22	mW/°C
Thermal resistance - junction to ambient*			
Any single die "on"		55.6	°C/W
Both die "on" equally		45.5	°C/W

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

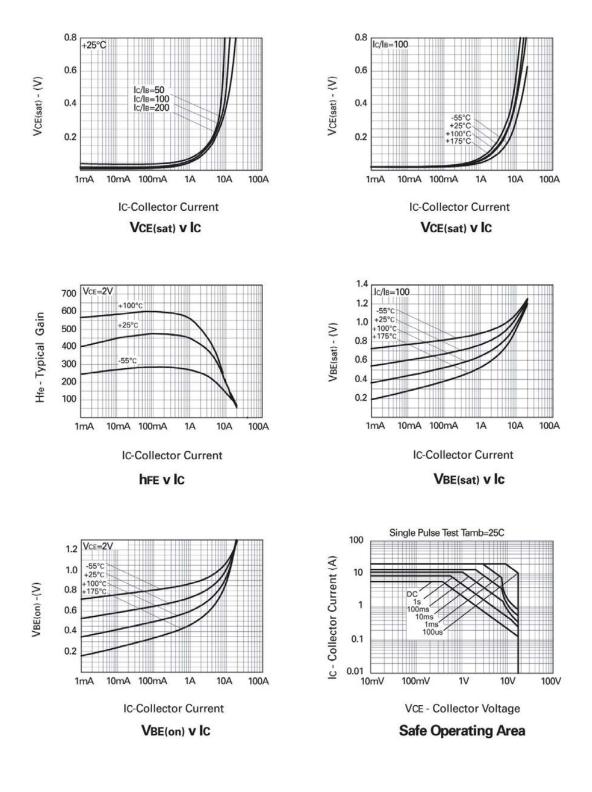
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	V _{(BR)CBO}	50	85		V	Ι _C =100μΑ
Collector-emitter breakdown voltage	V _{CES}	50	85		V	Ι _C =100μΑ
Collector-emitter breakdown voltage	V _{CEO}	17.5	24		V	I _C =10mA
Collector-emitter breakdown voltage	V _{CEV}	50	85		V	I _C =100μA, V _{EB} =1V
Emitter-base breakdown voltage	V _{(BR)EBO}	5	8.7		V	Ι _Ε =100μΑ
Collector cut-off current	I _{CBO}		0.3	10	nA	V _{CB} =35V
Emitter cut-off current	I _{EBO}		0.3	10	nA	V _{EB} =4V
Collector-emitter cut-off current	I _{CES}		0.3	10	nA	I _{CES} =35V
Collector-emitter saturation voltage	V _{CE(sat)}		27 55 120 200 200	45 75 160 240 300	mV mV mV mV mV	$\begin{split} _{C} = & 0.5A, \ _{B} = 10mA^{(*)} \\ _{C} = & 1A, \ _{B} = 10mA^{(*)} \\ _{C} = & 2A, \ _{B} = & 10mA^{(*)} \\ _{C} = & 5A, \ _{B} = & 100mA^{(*)} \\ _{C} = & 5A, \ _{B} = & 50mA^{(*)} \end{split}$
Base-emitter saturation voltage	V _{BE(sat)}		1000	1100	mV	I _C =5A, I _B =100mA ^(*)
Base-emitter turn on voltage	V _{BE(on)}		900	1000	mV	I _C =5A, V _{CE} =2V ^(*)
Static forward current transfer ratio	h _{FE}	280 300 300 250 50	440 450 450 300 80	1200		$I_{C}=10mA, V_{CE}=2V^{(*)}$ $I_{C}=0.5A, V_{CE}=2V^{(*)}$ $I_{C}=1A, V_{CE}=2V^{(*)}$ $I_{C}=5A, V_{CE}=2V^{(*)}$ $I_{C}=20A, V_{CE}=2V^{(*)}$
Transition frequency	f _T		150		MHz	I _C =50mA, V _{CE} =10V f=50MHz
Output capacitance	C _{obo}		60	80	pF	V _{CB} =10V, f=1MHz
Switching times	t _{on}		120		ns	I _C =4A, I _B =40mA,V _{CC} =10V
	t _{off}		250		ns	I_{C} =4A, I_{B} =±40mA, V_{CC} =10V

Electrical characteristics (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

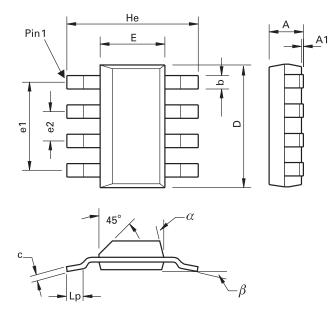
NOTES:

(*) Measured under pulsed conditions. Pulse width=300 $\mu s.$ Duty cycle $\leq 2\%$

Typical characteristics



Package outline - SM8



DIM	N	lillimete	rs	Inches		DIM	Millimeters		Inches				
	Min.	Max.	Тур.	Min.	Max.	Тур.		Min.	Max.	Тур.	Min.	Max.	Тур.
А	-	1.7	-	-	0.067	-	e1	-	-	4.59	-	-	0.1807
A1	0.02	0.1	-	0.0008	0.004	-	e2	-	-	1.53	-	-	0.0602
b	-	-	0.7	-	-	0.0275	He	6.7	7.3	-	0.264	0.287	-
С	0.24	0.32	-	0.009	0.013	-	Lp	0.9	-	-	0.035	-	-
D	6.3	6.7	-	0.248	0.264	-	α	-	15°	-	-	15°	-
E	3.3	3.7	-	0.130	0.145	-	β	-	-	10°	-	-	10°

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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